

GenX3™ 1200V IGBT

IXGA20N120B3

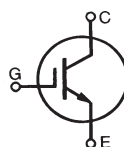
IXGP20N120B3

$$V_{CES} = 1200V$$

$$I_{C90} = 20A$$

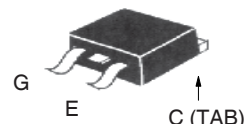
$$V_{CE(sat)} \leq 3.1V$$

High Speed Low Vsat PT
IGBTs 3-20 kHz Switching

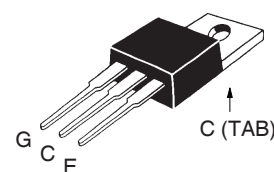


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	36	A
I_{C90}	$T_C = 90^\circ C$	20	A
I_{CM}	$T_C = 25^\circ C$, 1ms	80	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 15\Omega$ Clamped Inductive load	$I_{CM} = 40$ @ $V_{CE} \leq 1200$	A V
P_C	$T_C = 25^\circ C$	180	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
M_d	Mounting Torque (TO-220)	1.13/10	Nm/lb.in.
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6mm (0.062 in.) from Case for 10s	260	$^\circ C$
Weight	TO-263	2.5	g
	TO-220	3.0	g

TO-263 (IXGA)



TO-220 (IXGP)



G = Gate C = Collector
E = Emitter TAB = Collector

Features

- Optimized for Low Conduction and Switching Losses
- Square RBSOA
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines
- Inductive Heating

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			25 μA 1 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 16A$, $V_{GE} = 15V$, Note 2 $T_J = 125^\circ C$		2.7 2.8	3.1 V V

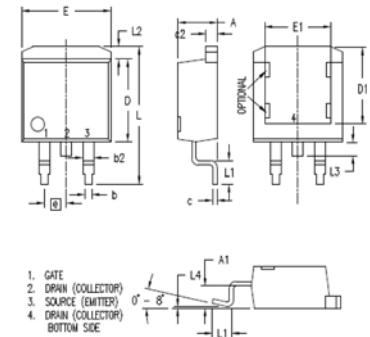
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 16\text{A}$, $V_{CE} = 10\text{V}$, Note 2	7.5	12.5	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		1070	pF
C_{oes}			80	pF
C_{res}			32	pF
Q_g	$I_C = 16\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		51	nC
Q_{ge}			7.4	nC
Q_{gc}			23	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 16\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 600\text{V}$, $R_G = 15\Omega$ Note 1		16	ns
t_{ri}			31	ns
E_{on}			0.92	mJ
$t_{d(off)}$			150	ns
t_{fi}			155	ns
E_{off}			0.56	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 16\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 600\text{V}$, $R_G = 15\Omega$ Note 1		16	ns
t_{ri}			45	ns
E_{on}			1.60	mJ
$t_{d(off)}$			180	ns
t_{fi}			540	ns
E_{off}			1.63	mJ
R_{thJC}	TO-220			0.69 $^\circ\text{C/W}$
R_{thCK}			0.50	$^\circ\text{C/W}$

- Notes:
- Switching Times may Increase for $V_{CE} \text{ (Clamp)} > 0.5 \cdot V_{CES}$, Higher T_J or Increased R_G .
 - Pulse Test, $t \leq 300\mu\text{s}$; Duty Cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

TO-263 (IXGA) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 (IXGP) Outline

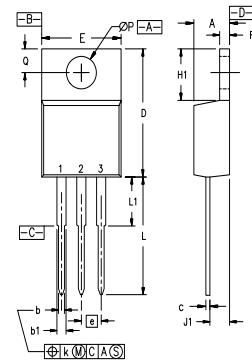


Fig. 1. Output Characteristics
@ 25°C

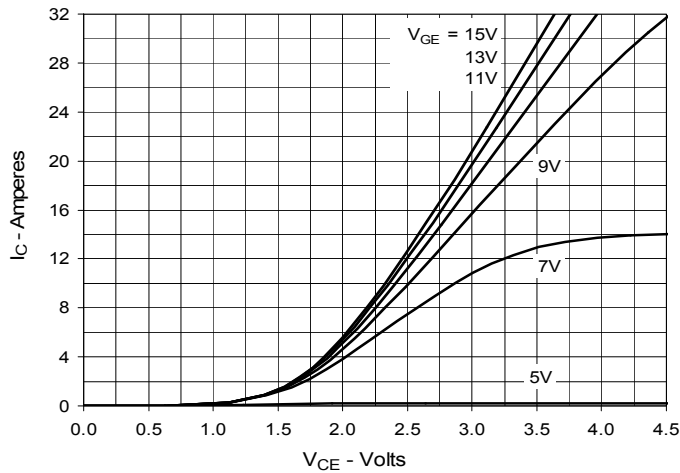


Fig. 2. Extended Output Characteristics
@ 25°C

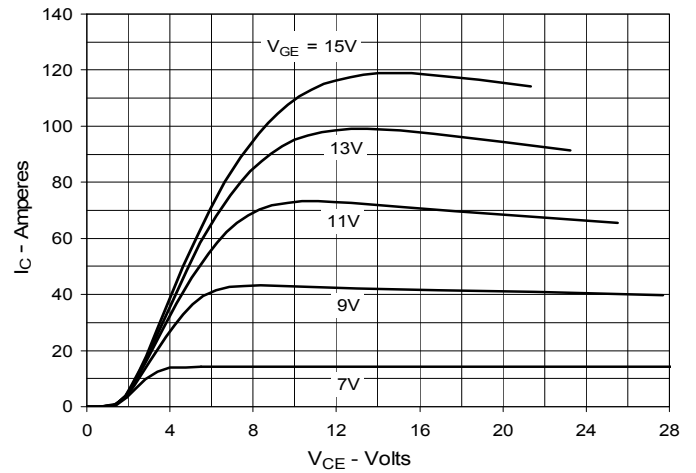


Fig. 3. Output Characteristics
@ 125°C

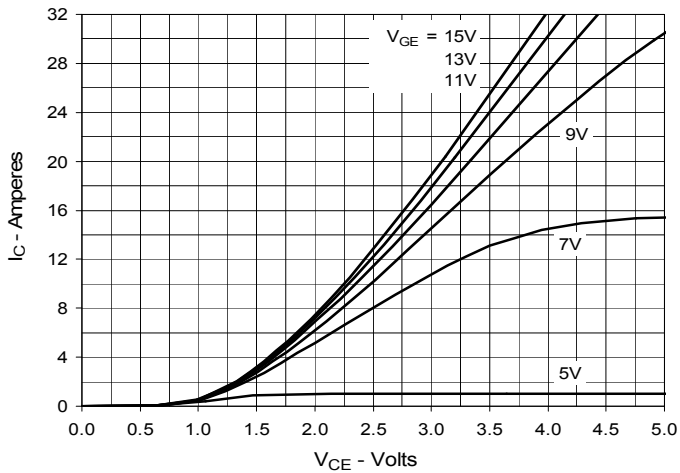


Fig. 4. Dependence of $V_{CE(sat)}$ on
Junction Temperature

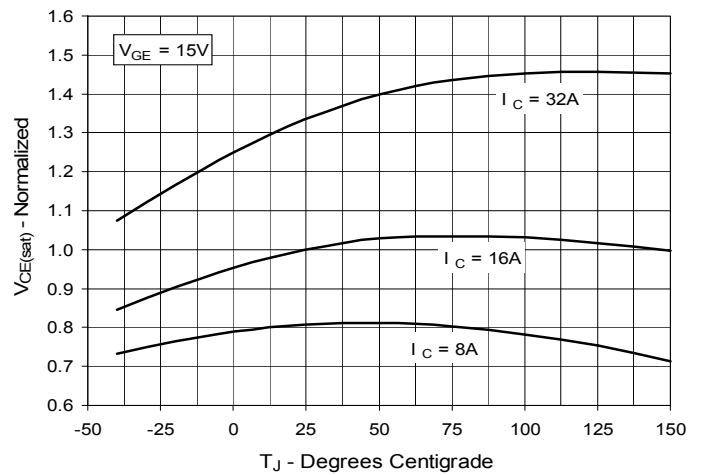


Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter Voltage

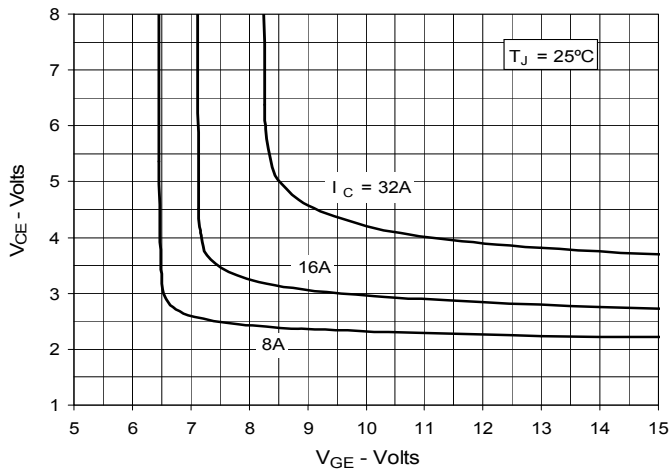


Fig. 6. Input Admittance

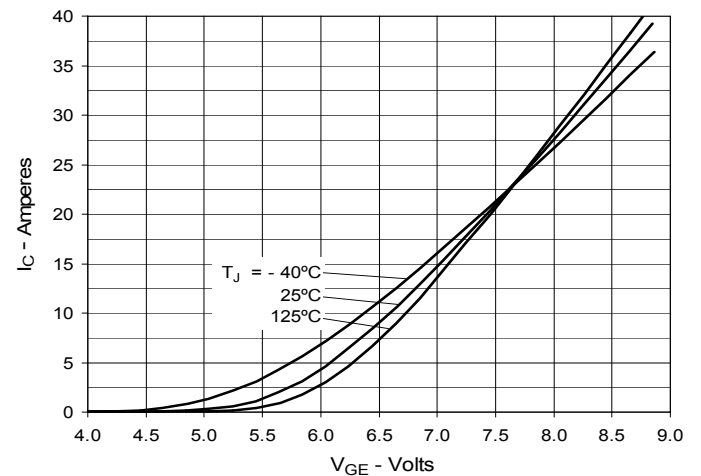


Fig. 7. Transconductance

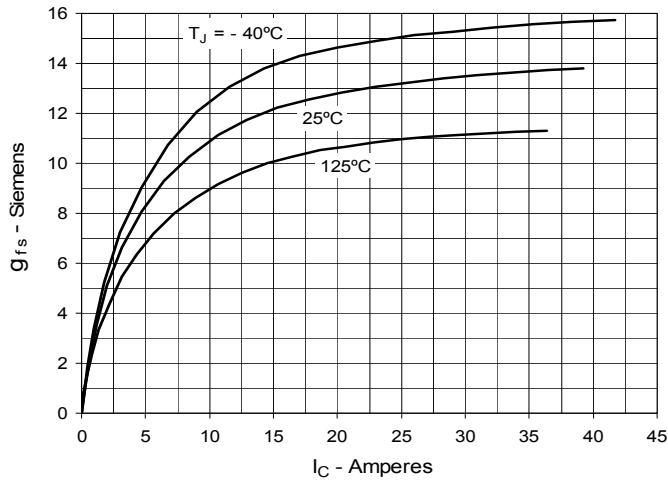


Fig. 8. Gate Charge

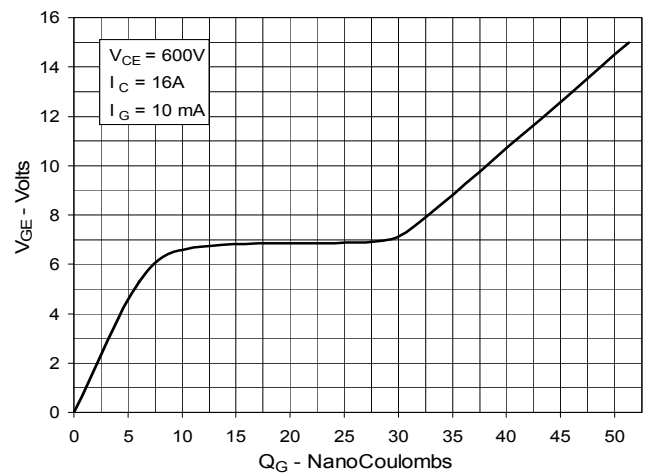


Fig. 9. Capacitance

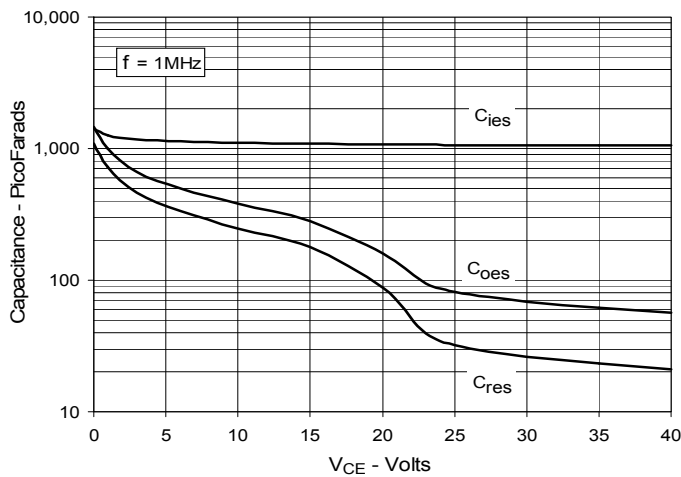


Fig. 10. Reverse-Bias Safe Operating Area

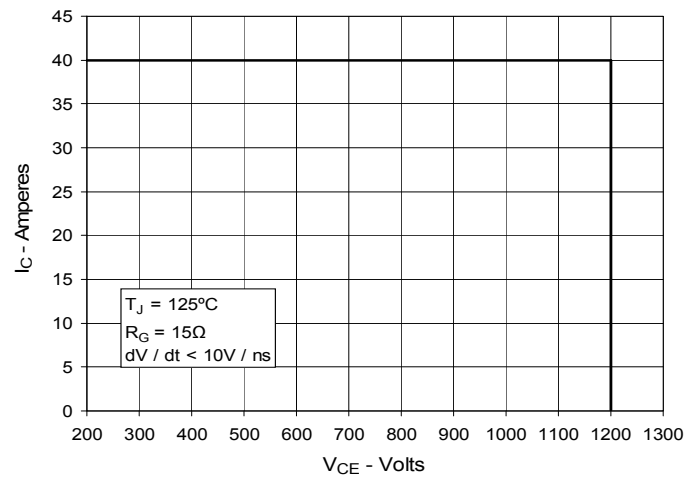
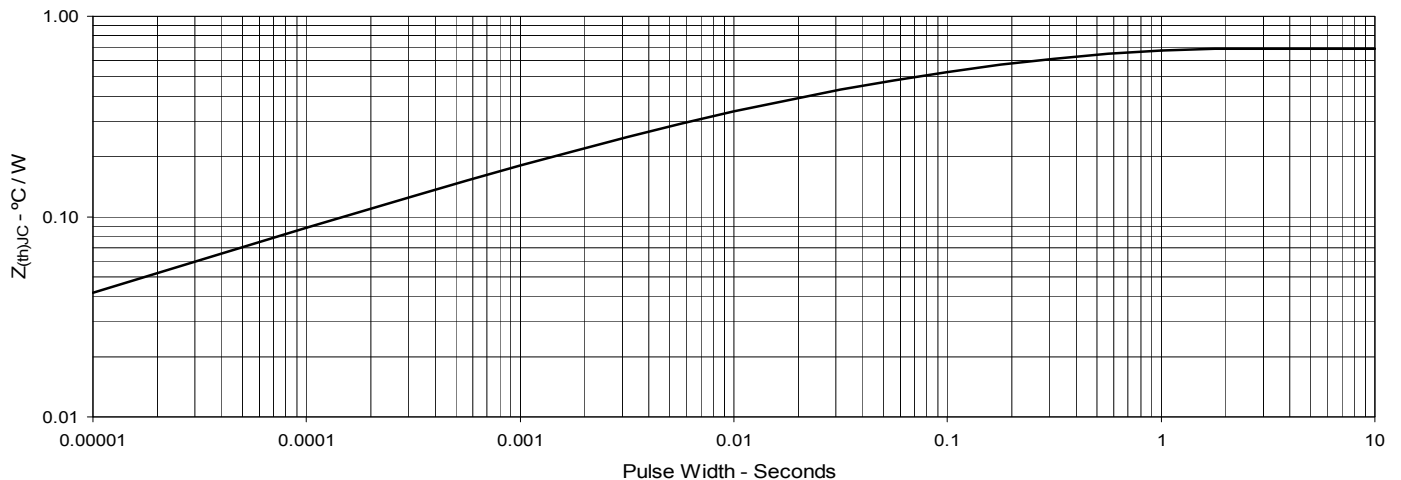
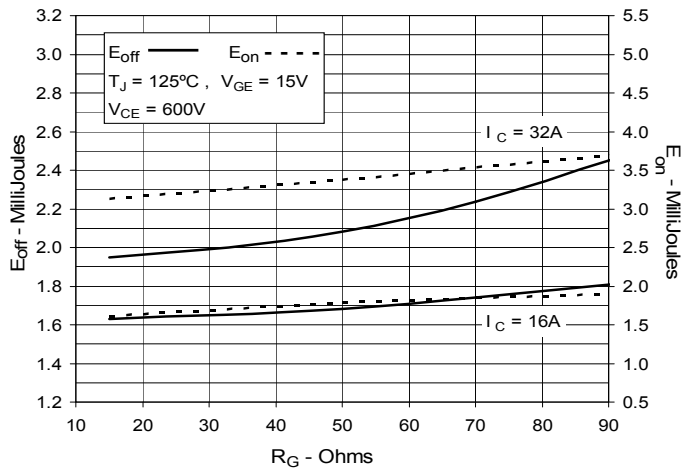


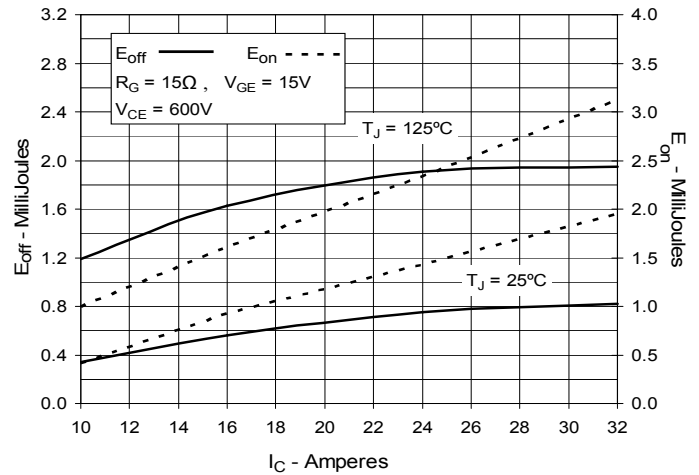
Fig. 11. Maximum Transient Thermal Impedance



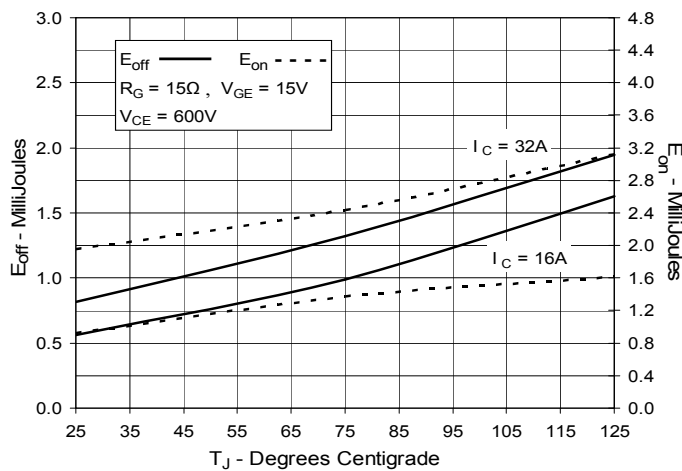
**Fig. 12. Inductive Switching
Energy Loss vs. Gate Resistance**



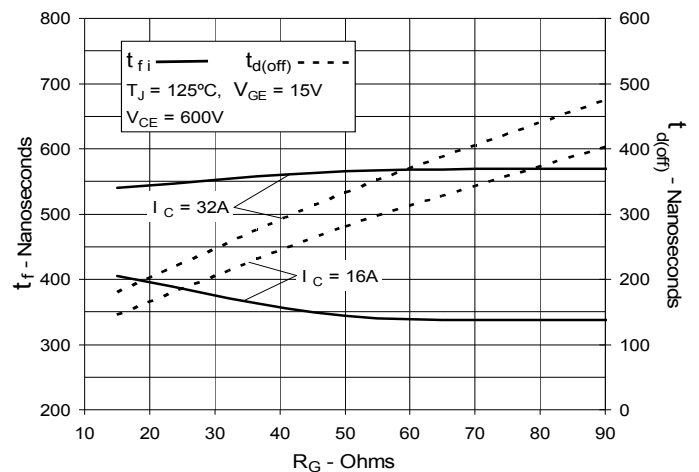
**Fig. 13. Inductive Switching
Energy Loss vs. Collector Current**



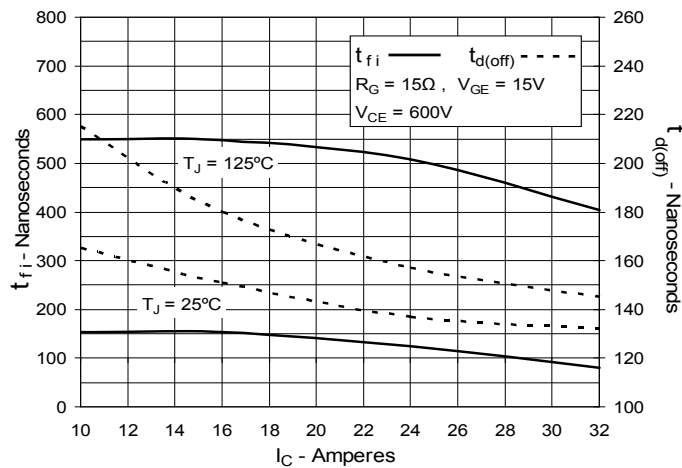
**Fig. 14. Inductive Switching
Energy Loss vs. Junction Temperature**



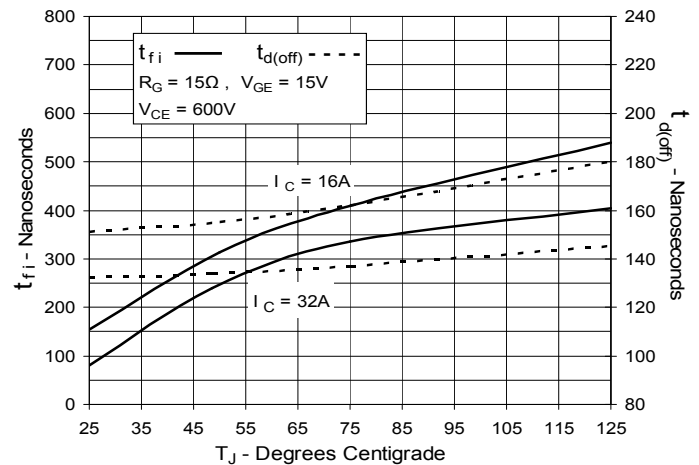
**Fig. 15. Inductive Turn-off
Switching Times vs. Gate Resistance**



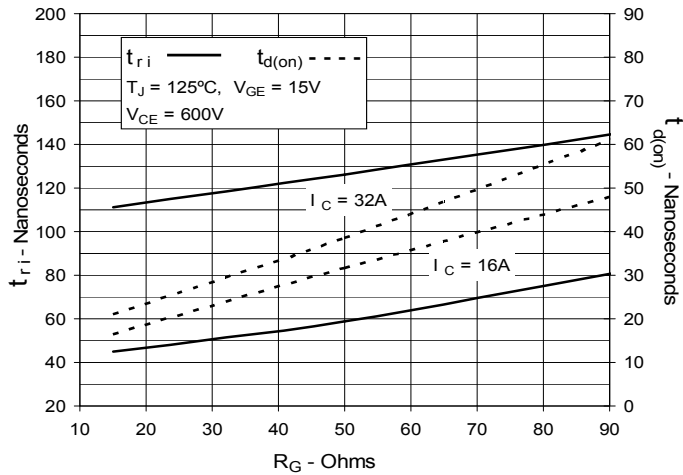
**Fig. 16. Inductive Turn-off
Switching Times vs. Collector Current**



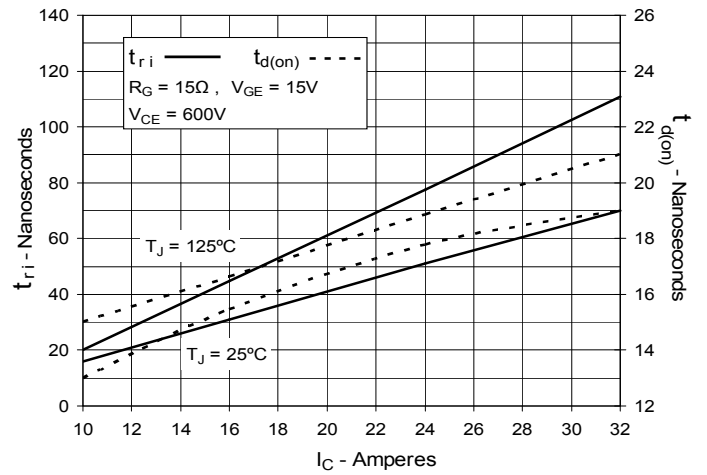
**Fig. 17. Inductive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature**

